## IN THE CLAIMS

Please cancel claims 1-6.

Please add the following new claims 7-52:

7. (New) A method of chemically mechanically polishing a substrate, said method comprising:

providing a semiconductor wafer substrate comprising a surface to be polished; and

contacting the surface with a polishing slurry comprising a first oxidizer and a second oxidizer, wherein the second oxidizer is different than the first oxidizer, and the slurry comprising the first and second oxidizers exhibits a synergistically increased substrate removal rate.

8. (New) The method of claim 7, wherein the slurry further comprises abrasive particles.

9. (New) The method of claim 8, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel one another.

10. (New) The method of claim 8, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel the surface to be polished.

11. (New) The method of claim 7, wherein the first oxidizer comprises ammonium persulfate and the second oxidizer comprises a peroxymonosulfate compound.

12. (New) The method of claim 7, wherein the first oxidizer comprises hydroxylamine nitrate and the second oxidizer comprises hydroxylamine.

13. (New) The method of claim 7, wherein the first oxidizer comprises from about 0.5% to about 10% hydroxylamine nitrate.

14. (New) The method of claim 7, wherein the first oxidizer comprises from about 2% to about 10% hydroxylamine nitrate.

15. (New) The method of claim 7, wherein the second oxidizer comprises from about 1% to about 10% hydroxylamine.

16. (New) The method of claim 7, wherein the first oxidizer comprises hydroxylamine nitrate and the second oxidizer comprises from about 0.005% to about 0.36% by weight hydroxylamine.

17. (New) The method of claim 7, wherein the first oxidizer comprises hydroxylamine nitrate and the second oxidizer comprises about 0.04% by weight hydroxylamine.

18. (New) The method of claim 7, wherein the first oxidizer comprises ammonium persulfate and the second oxidizer comprises from about 0.5% to about 2% periodic acid.

19. (New) The method of claim 7, wherein the first oxidizer comprises hydrogen peroxide and the second oxidizer comprises hydroxylamine.

20. (New) The method of claim 7, wherein the first oxidizer comprises hydrogen peroxide and the second oxidizer comprises from about 1% to about 10% hydroxylamine.

21. (New) The method of claim 7, wherein the first oxidizer comprises ammonium persulfate and the second oxidizer comprises potassium periodate.

22. (New) The method of claim 7, wherein the first oxidizer comprises ammonium persulfate and the second oxidizer comprises potassium iodate.

23. (New) The method of claim 7, wherein the first oxidizer comprises ammonium persulfate and the second oxidizer comprises periodic acid.

24. (New) A method of chemically mechanically polishing a substrate, said method comprising:

providing a substrate comprising a surface to be polished, wherein the substrate is a metal, a dielectric material or a combination thereof; and

contacting the surface with a polishing slurry comprising about 0.1 molar hydroxylamine and abrasive particles.

25. (New) The method of claim 24, wherein the abrasive particles comprise fumed silica.

26. (New) The method of claim 24, wherein the abrasive particles comprise colloidal silica.

27. (New) The method of claim 24, wherein the surface is tetraethylorthosilicate (TEOS), boron-phosphorous spin-on glass (BPSG), phosphorous spin-on glass (PSG) or spin-on glass (SOG).

28. (New) The method of claim 24, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel one another.

29. (New) The method of claim 24, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel the surface.

30. (New) A method of chemically mechanically polishing a substrate, said method comprising:

providing a substrate comprising a surface to be polished, wherein the substrate is a metal and a dielectric material; and contacting the surface with a polishing slurry comprising from about 2% to about 10% hydroxylamine and abrasive particles.

31. (New) The method of claim 30, wherein the abrasive particles comprise fumed silica.

32. (New) The method of claim 30, wherein the abrasive particles comprise colloidal silica, and wherein the polishing slurry has a pH below 8.

33. (New) The method of claim 30, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel the surface.

34. (New) The method of claim 30, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel one another.

35. (New) A method of chemically mechanically polishing a substrate, said method comprising:

providing a substrate comprising a surface to be polished, wherein the substrate is a metal, a dielectric material or a combination thereof; and

contacting the surface with a polishing slurry comprising a first oxidizer and a second oxidizing compound, wherein the second oxidizing compound is an indirect source of hydrogen peroxide.

36. (New) The method of claim 35, wherein the first oxidizer is hydroxylamine, a hydroxylamine derivative or a hydroxylamine salt.

37. (New) The method of claim 35, wherein the second oxidizer comprises from about 1% to about 10% hydroxylamine.

38. (New) The method of claim 36, wherein the hydroxylamine derivative is hydroxylamine nitrate.

39. (New) The method of claim 35, wherein the first oxidizer comprises from about 0.5% to about 10% hydroxylamine nitrate.

40. (New) The method of claim 35, wherein the first oxidizer comprises from about 2% to about 10% hydroxylamine nitrate.

41. (New) The method of claim 35, wherein the second oxidizing compound is a perborate.

42. (New) The method of claim 35, wherein the second oxidizing compound is sodium perborate tetrahydrate.

43. (New) The method of claim 35, wherein the slurry further comprises a pH-adjusting compound.

44. (New) The method of claim 35, wherein the slurry further comprises abrasive particles.

45. (New) The method of claim 44, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel one another.

46. (New) The method of claim 44, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel the surface.

47. (New) A method of chemically mechanically polishing a substrate, said method comprising:

providing a substrate comprising a surface to be polished, wherein the substrate comprises tungsten; and

contacting the surface with a polishing slurry comprising 2% urea hydrogen peroxide and an abrasive.

48. (New) A method of chemically mechanically polishing a substrate, said method comprising:

providing a substrate comprising a surface to be polished, wherein the substrate comprises copper; and

contacting the surface with a polishing slurry comprising about 10% hydroxylamine nitrate, water, and a silica abrasive, wherein the slurry comprises between about 56 ppm copper to about 71 ppm copper when polishing the surface.

49. (New) A method of chemically mechanically polishing a substrate, said method comprising:

providing a substrate having a surface comprising a metal and a dielectric material; and

contacting the surface with an aqueous polishing slurry comprising from about 0.005% to about 0.36% by weight hydroxylamine and an abrasive.

50. (New) The method of claim 49, wherein the polishing slurry comprises about 0.005% by weight hydroxylamine.

51. (New) The method of claim 49, wherein the polishing slurry comprises about 0.04% by weight hydroxylamine.

52. (New) The method of claim 49, wherein the polishing slurry comprises about 0.36% by weight hydroxylamine.